



Future Normal in Semiconductor

2025년 2월 13일(목), 10:55-12:40

Room C(컨벤션홀 L), 5층

D. Thin Film Process Technology 분과

015_[TC2-D] Emerging Devices - II

좌장: 손준우 교수(서울대학교), 최병준 교수(서울과학기술대학교)

<p>초청 TC2-D-1 10:55-11:25</p>	<p>Interface-Type Memristor Devices Based on Transition Metal Oxides Synthesized via Atomic Layer Deposition Minjae Kim School of Materials Science and Engineering, Yeungnam University</p>
<p>TC2-D-2 11:25-11:40</p>	<p>The Influence of Plasma Energy for the Interface Layer Deposition on the Resistance Switching Properties of a-IGZO-Based Memory Devices Haripriya G. R.¹, Hee Yeon Noh¹, Yerim Kim¹, Hyunki Lee², June-Seo Kim¹, Myoung-Jae Lee¹, and Hyeon-Jun Lee^{1,2} ¹Division of Nanotechnology, DGIST, ²Division of Intelligent Robotics, DGIST</p>
<p>TC2-D-3 11:40-11:55</p>	<p>Electronic Threshold Switching of As-SiO₂ Selector: Charged Oxygen Vacancy Model Hye Rim Kim¹, Tae Jun Seok¹, Tae Jung Ha², Jeong Hwan Song², Kyun Seong Dae³, Sang Gil Lee³, Hyun Seung Choi¹, Su Yong Park¹, Byung Joon Choi⁴, Jae Hyuck Jang³, Soo Gil Kim², and Tae Joo Park¹ ¹Department of Materials Science and Chemical Engineering, Hanyang University, ²SK hynix Inc., ³Electron Microscopy and Spectroscopy Team, KBSI, ⁴Department of Materials Science and Engineering, Seoul National University of Science and Technology</p>
<p>TC2-D-4 11:55-12:10</p>	<p>High-Reliability Leaky-Integrate-and-Fire Neuron Devices Enabled by Carbon Doping for Holding Voltage Control and Their Applications Jeong Hwan Song and Kim Gun Hwan Department of System Semiconductor Engineering, Yonsei University</p>
<p>TC2-D-5 12:10-12:25</p>	<p>Polarity-Dependent Memory Effect and Its Conduction Mechanism in Ovonic Threshold Switch Hyun Wook Kim, Ju Hwan Park, Se Hwan Jeon, Yoon Jae Hong, and Byung Joon Choi Department of Materials Science and Engineering, Seoul National University of Science and Technology</p>



제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

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TC2-D-6 12:25-12:40	Reliability Characteristics of GeSbSeTe Devices According to In Doping Concentration Soohyun-Lee and Gun Hwan Kim Yonsei University
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